Semiconductors, Dielectrics, and Metals for Nanoelectronics 11

Editors:

S. Kar
Indian Institute of Technology
Kolkata, India

S. Van Elshocht
IMEC
Leuven, Belgium

K. Kita
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H. Jagannathan
IBM Research
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M. Houssa
University of Leuven
Leuven, Belgium

D. Misra
New Jersey Institute of Technology
Newark, New Jersey, USA

D. Landheer
National Research Council Canada
Ottawa, Ontario, Canada

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